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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

etails oduct Status	Active
ore Processor	RL78
ore Size	16-Bit
eed	32MHz
onnectivity	CSI, I ² C, LINbus, UART/USART
-	
ripherals	DMA, LVD, POR, PWM, WDT
umber of I/O	82
ogram Memory Size	96KB (96K x 8)
ogram Memory Type	FLASH
PROM Size	•
AM Size	8K x 8
ltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
ata Converters	A/D 20x8/10b
scillator Type	Internal
perating Temperature	-40°C ~ 85°C (TA)
ounting Type	Surface Mount
ckage / Case	100-LQFP
pplier Device Package	100-LQFP (14x14)
rchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f101pfafb-30

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RL78/G13 1. OUTLINE

Table 1-1. List of Ordering Part Numbers

(2/12)

				(2/12)
Pin	Package	Data	Fields of	Ordering Part Number
count		flash	Application	
			Note	
25 pins	25-pin plastic	Mounted	Α	R5F1008AALA#U0, R5F1008CALA#U0, R5F1008DALA#U0,
25 pins	· · ·	Mounted	7.	R5F1008EALA#U0
	WFLGA (3 \times 3 mm,			R5F1008AALA#W0, R5F1008CALA#W0, R5F1008DALA#W0,
	0.5 mm pitch)			R5F1008EALA#W0
			G	R5F1008AGLA#U0, R5F1008CGLA#U0, R5F1008DGLA#U0,
				R5F1008EGLA#U0
				R5F1008AGLA#W0, R5F1008CGLA#W0, R5F1008DGLA#W0,
				R5F1008EGLA#W0
		Not	Α	R5F1018AALA#U0, R5F1018CALA#U0, R5F1018DALA#U0,
i		mounted		R5F1018EALA#U0
				R5F1018AALA#W0, R5F1018CALA#W0, R5F1018DALA#W0,
				R5F1018EALA#W0
30 pins	30-pin plastic LSSOP	Mounted	Α	R5F100AAASP#V0, R5F100ACASP#V0, R5F100ADASP#V0,
i	(7.62 mm (300), 0.65			R5F100AEASP#V0, R5F100AFASP#V0, R5F100AGASP#V0
	mm pitch)			R5F100AAASP#X0, R5F100ACASP#X0, R5F100ADASP#X0
	min piton)		_	R5F100AEASP#X0, R5F100AFASP#X0, R5F100AGASP#X0
			D	R5F100AADSP#V0, R5F100ACDSP#V0, R5F100ADDSP#V0,
				R5F100AEDSP#V0, R5F100AFDSP#V0, R5F100AGDSP#V0
				R5F100AADSP#X0, R5F100ACDSP#X0, R5F100ADDSP#X0, R5F100AEDSP#X0, R5F100AFDSP#X0, R5F100AGDSP#X0
			G	R5F100AGSP#V0, R5F100ACGSP#V0,
			G	R5F100ADGSP#V0, R5F100ACGSF#V0,
				R5F100AFGSP#V0, R5F100AGGSP#V0,
				R5F100AAGSP#X0, R5F100ACGSP#X0,
				R5F100ADGSP#X0,R5F100AEGSP#X0,
				R5F100AFGSP#X0, R5F100AGGSP#X0
		Not	Α	R5F101AAASP#V0, R5F101ACASP#V0, R5F101ADASP#V0,
				R5F101AEASP#V0, R5F101AFASP#V0, R5F101AGASP#V0
		mounted		R5F101AAASP#X0, R5F101ACASP#X0, R5F101ADASP#X0,
				R5F101AEASP#X0, R5F101AFASP#X0, R5F101AGASP#X0
			D	R5F101AADSP#V0, R5F101ACDSP#V0, R5F101ADDSP#V0,
				R5F101AEDSP#V0, R5F101AFDSP#V0, R5F101AGDSP#V0
				R5F101AADSP#X0, R5F101ACDSP#X0, R5F101ADDSP#X0,
				R5F101AEDSP#X0, R5F101AFDSP#X0, R5F101AGDSP#X0
32 pins	32-pin plastic	Mounted	Α	R5F100BAANA#U0, R5F100BCANA#U0, R5F100BDANA#U0,
	HWQFN (5 × 5 mm,			R5F100BEANA#U0, R5F100BFANA#U0, R5F100BGANA#U0
	0.5 mm pitch)			R5F100BAANA#W0, R5F100BCANA#W0, R5F100BDANA#W0,
	0.5 min pitch)			R5F100BEANA#W0, R5F100BFANA#W0, R5F100BGANA#W0
			D	R5F100BADNA#U0, R5F100BCDNA#U0, R5F100BDDNA#U0,
				R5F100BEDNA#U0, R5F100BFDNA#U0, R5F100BGDNA#U0
				R5F100BADNA#W0, R5F100BCDNA#W0, R5F100BDDNA#W0,
				R5F100BEDNA#W0, R5F100BFDNA#W0, R5F100BGDNA#W0
			G	R5F100BAGNA#U0, R5F100BCGNA#U0, R5F100BDGNA#U0,
				R5F100BEGNA#U0, R5F100BFGNA#U0, R5F100BGGNA#U0
				R5F100BAGNA#W0, R5F100BCGNA#W0, R5F100BDGNA#W0,
			_	R5F100BEGNA#W0, R5F100BFGNA#W0, R5F100BGGNA#W0
		Not	Α	R5F101BAANA#U0, R5F101BCANA#U0, R5F101BDANA#U0,
		mounted		R5F101BEANA#U0, R5F101BFANA#U0, R5F101BGANA#U0
				R5F101BAANA#W0, R5F101BCANA#W0, R5F101BDANA#W0,
			D	R5F101BEANA#W0, R5F101BFANA#W0, R5F101BGANA#W0
			٦ ا	R5F101BADNA#U0, R5F101BCDNA#U0, R5F101BDDNA#U0, R5F101BEDNA#U0, R5F101BEDNA#U0
1				R5F101BADNA#W0, R5F101BCDNA#W0, R5F101BDDNA#W0,
				R5F101BEDNA#W0, R5F101BCDNA#W0, R5F101BBDNA#W0,
			1	TOT TO TO EDINA#WO, NOT TO TO FOUNA#WO, NOT TO TO EDINA#WO

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

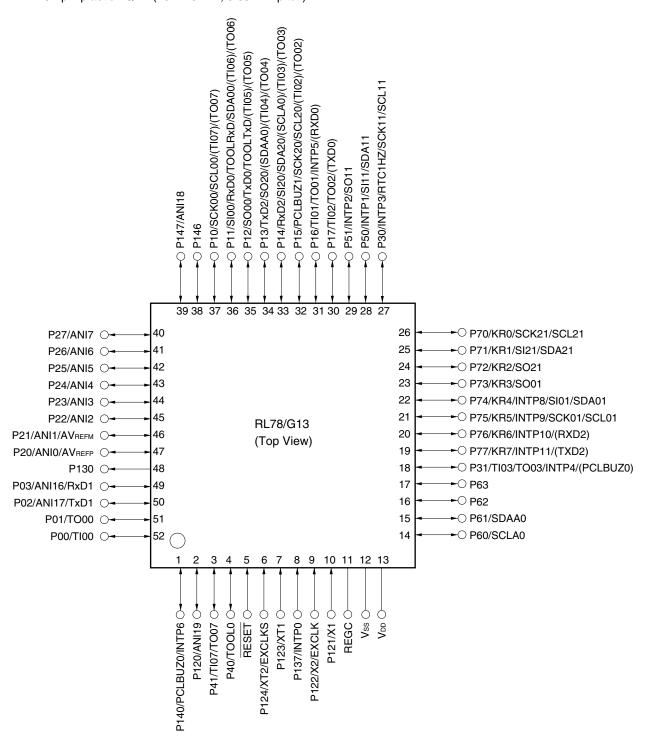
Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



RL78/G13 1. OUTLINE

1.3.10 52-pin products

• 52-pin plastic LQFP (10 × 10 mm, 0.65 mm pitch)



Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

2.2 Oscillator Characteristics

2.2.1 X1, XT1 oscillator characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation	Ceramic resonator/	Ceramic resonator/ $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$			20.0	MHz
frequency (fx) ^{Note}	crystal resonator	$2.4~V \leq V_{DD} < 2.7~V$	1.0		16.0	MHz
		$1.8~V \leq V_{DD} < 2.4~V$	1.0		8.0	MHz
		$1.6~V \leq V_{DD} < 1.8~V$	1.0		4.0	MHz
XT1 clock oscillation frequency (fx) ^{Note}	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator and XT1 oscillator, refer to 5.4 System Clock Oscillator.

2.2.2 On-chip oscillator characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Oscillators	Parameters		MIN.	TYP.	MAX.	Unit	
High-speed on-chip oscillator clock frequency Notes 1, 2	fін			1		32	MHz
High-speed on-chip oscillator		–20 to +85 °C	$1.8~V \leq V_{DD} \leq 5.5~V$	-1.0		+1.0	%
clock frequency accuracy			$1.6~V \leq V_{DD} < 1.8~V$	-5.0		+5.0	%
		–40 to −20 °C	$1.8~V \leq V_{DD} \leq 5.5~V$	-1.5		+1.5	%
			$1.6~V \le V_{DD} < 1.8~V$	-5.5		+5.5	%
Low-speed on-chip oscillator clock frequency	fıL				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		+15	%

Notes 1. High-speed on-chip oscillator frequency is selected by bits 0 to 3 of option byte (000C2H/010C2H) and bits 0 to 2 of HOCODIV register.

2. This indicates the oscillator characteristics only. Refer to AC Characteristics for instruction execution time.

2.3 DC Characteristics

2.3.1 Pin characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (1/5)$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high ^{Note 1}	Іон1	Per pin for P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	$1.6~V \le EV_{DD0} \le 5.5~V$			-10.0 Note 2	mA
		Total of P00 to P04, P07, P32 to P37,	$4.0~V \leq EV_{DD0} \leq 5.5~V$			-55.0	mA
		P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	$2.7~V \leq EV_{DD0} < 4.0~V$			-10.0	mA
		$(When duty \le 70\%^{Note 3})$	$1.8~V \leq EV_{DD0} < 2.7~V$			-5.0	mA
			$1.6~V \leq EV_{DD0} < 1.8~V$			-2.5	mA
		Total of P05, P06, P10 to P17, P30, P31,				-80.0	mA
		P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to	$2.7~V \leq EV_{DD0} < 4.0~V$			-19.0	mA
		P117, P146, P147	$1.8~V \leq EV_{DD0} < 2.7~V$			-10.0	mA
		(When duty $\leq 70\%$ Note 3)	$1.6~V \leq EV_{DD0} < 1.8~V$			-5.0	mA
		Total of all pins (When duty ≤ 70% Note 3)	$1.6~V \leq EV_{DD0} \leq 5.5~V$			-135.0 Note 4	mA
	І он2	Per pin for P20 to P27, P150 to P156	$1.6~V \leq V_{DD} \leq 5.5~V$			-0.1 Note 2	mA
		Total of all pins (When duty ≤ 70% Note 3)	$1.6~V \leq V_{DD} \leq 5.5~V$			-1.5	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from the EV_{DD0}, EV_{DD1}, V_{DD} pins to an output pin.
 - 2. However, do not exceed the total current value.
 - 3. Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = $(IOH \times 0.7)/(n \times 0.01)$

<Example> Where n = 80% and loh = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \cong -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

4. The applied current for the products for industrial application (R5F100xxDxx, R5F101xxDxx, R5F100xxGxx) is -100 mA.

Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ (3/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V _{IH1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147		0.8EV _{DD0}		EV _{DD0}	V
	V _{IH2}	P01, P03, P04, P10, P11, P13 to P17, P43, P44, P53 to P55,	TTL input buffer 4.0 V ≤ EV _{DD0} ≤ 5.5 V	2.2		EV _{DD0}	V
		P80, P81, P142, P143	TTL input buffer $3.3 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}$	2.0		EV _{DD0}	V
			TTL input buffer 1.6 V ≤ EV _{DD0} < 3.3 V	1.5		EV _{DD0}	V
	V _{IH3}	P20 to P27, P150 to P156		0.7V _{DD}		V _{DD}	٧
	V _{IH4}	P60 to P63		0.7EV _{DD0}		6.0	٧
	V _{IH5}	P121 to P124, P137, EXCLK, EXCL	0.8V _{DD}		V _{DD}	٧	
Input voltage, low	V _{IL1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	,	0		0.2EV _{DD0}	V
	V _{IL2}	P01, P03, P04, P10, P11, P13 to P17, P43, P44, P53 to P55,	TTL input buffer 4.0 V ≤ EV _{DD0} ≤ 5.5 V	0		0.8	V
		P80, P81, P142, P143	TTL input buffer 3.3 V ≤ EV _{DD0} < 4.0 V	0		0.5	V
			TTL input buffer 1.6 V ≤ EV _{DD0} < 3.3 V	0		0.32	V
	V _{IL3}	P20 to P27, P150 to P156		0		0.3V _{DD}	٧
	V _{IL4}	P60 to P63		0		0.3EV _{DD0}	٧
	V _{IL5}	P121 to P124, P137, EXCLK, EXCL	KS, RESET	0		0.2V _{DD}	٧

Caution The maximum value of V_{IH} of pins P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 is EV_{DD0}, even in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

- Notes 1. Total current flowing into VDD, EVDDO, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDO, and EVDD1, or Vss, EVsso, and EVss1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - **5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

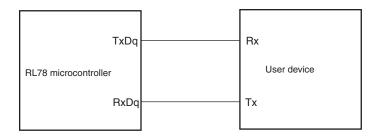
HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz}$ to 32 MHz

 $2.4~V \leq V_{DD} \leq 5.5~V @ 1~MHz$ to 16 MHz

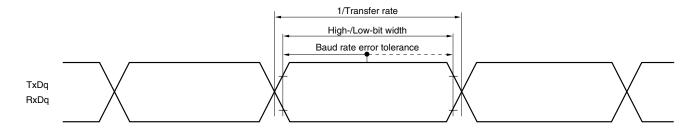
LS (low-speed main) mode: $1.8~V \le V_{DD} \le 5.5~V~@1~MHz$ to 8~MHz LV (low-voltage main) mode: $1.6~V \le V_{DD} \le 5.5~V~@1~MHz$ to 4~MHz

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remarks 1. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)

2. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,n: Channel number (mn = 00 to 03, 10 to 13))

(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.7 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

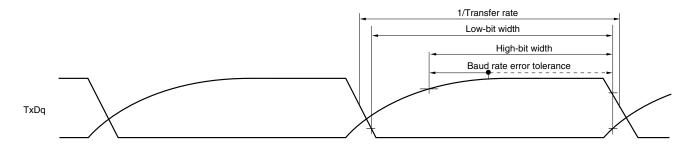
Parameter	Symbol	Conditions		Conditions HS (high-speed I main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t KCY1	tkcy1 ≥ 2/fclk	$4.0~V \leq EV_{DD0} \leq 5.5~V$	62.5		250		500		ns
			$2.7~V \leq EV_{DD0} \leq 5.5~V$	83.3		250		500		ns
SCKp high-/low-level width	tкн1, tкL1	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$		tксү1/2 — 7		tксү1/2 – 50		tксү1/2 — 50		ns
		2.7 V ≤ EV _{DI}	00 ≤ 5.5 V	tксү1/2 – 10		tксү1/2 — 50		tксү1/2 — 50		ns
SIp setup time (to SCKp↑)	tsıĸı	4.0 V ≤ EV _{DI}	00 ≤ 5.5 V	23		110		110		ns
Note 1		2.7 V ≤ EV _{DI}	00 ≤ 5.5 V	33		110		110		ns
SIp hold time (from SCKp [↑]) Note 2	tksı1	2.7 V ≤ EV _{DD0} ≤ 5.5 V		10		10		10		ns
Delay time from SCKp↓ to SOp output Note 3	tkso1	C = 20 pF No	te 4		10		10		10	ns

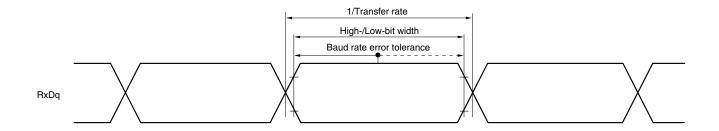
- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- Remarks 1. This value is valid only when CSI00's peripheral I/O redirect function is not used.
 - p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0),g: PIM and POM numbers (g = 1)
 - 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,n: Channel number (mn = 00))

UART mode bit width (during communication at different potential) (reference)





- $\begin{tabular}{ll} \begin{tabular}{ll} \bf R_b[\Omega]: Communication line (TxDq) pull-up resistance, \\ C_b[F]: Communication line (TxDq) load capacitance, V_b[V]: Communication line voltage \\ \end{tabular}$
 - 2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
 - 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))
 - **4.** UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

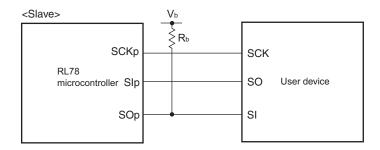
(7) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only) (1/2)

(Ta = -40 to +85°C, 2.7 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol		Conditions	HS (hig		LS (low main)	-speed	LV (low- main)	•	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 2/fclk	$ \begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 20 \; pF, \; R_b = 1.4 \\ &k\Omega \end{aligned} $	200		1150		1150		ns
			$\begin{split} & 2.7 \; \text{V} \leq \text{EV}_{\text{DD0}} < 4.0 \; \text{V}, \\ & 2.3 \; \text{V} \leq \text{V}_{\text{b}} \leq 2.7 \; \text{V}, \\ & C_{\text{b}} = 20 \; \text{pF}, \; R_{\text{b}} = 2.7 \\ & \text{k}\Omega \end{split}$	300		1150		1150		ns
SCKp high-level width	tкнı	$4.0 \text{ V} \leq \text{EV}_{DD}$ $2.7 \text{ V} \leq \text{V}_{b} \leq 6$ $C_{b} = 20 \text{ pF, F}$	4.0 V,	tксү1/2 — 50		tксу1/2 — 50		tксү1/2 — 50		ns
		$ 2.7 \text{ V} \leq \text{EV}_{\text{DDO}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ C_{\text{b}} = 20 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega $		tксу1/2 — 120		tксу1/2 — 120		tксу1/2 — 120		ns
SCKp low-level width	tĸL1	$\begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 20 \ pF, \ R_b = 1.4 \ k\Omega \end{aligned}$		tксү1/2 — 7		t _{KCY1} /2 – 50		t _{KCY1} /2 – 50		ns
		$2.7 \text{ V} \leq \text{EV}_{DD}$ $2.3 \text{ V} \leq \text{V}_{b} \leq 3$ $C_{b} = 20 \text{ pF, F}$	2.7 V,	tксу ₁ /2 – 10		tксү1/2 — 50		tксү1/2 — 50		ns
SIp setup time (to SCKp↑) Note 1	tsıĸı	$4.0 \text{ V} \leq \text{EV}_{DD}$ $2.7 \text{ V} \leq \text{V}_{b} \leq 4$ $C_{b} = 20 \text{ pF, F}$	4.0 V,	58		479		479		ns
		$2.7 \text{ V} \leq \text{EV}_{DD}$ $2.3 \text{ V} \leq \text{V}_{b} \leq 2$ $C_{b} = 20 \text{ pF, F}$	2.7 V,	121		479		479		ns
SIp hold time (from SCKp↑) Note 1	tksi1	$4.0 \text{ V} \leq \text{EV}_{DD}$ $2.7 \text{ V} \leq \text{V}_{b} \leq 4$ $C_{b} = 20 \text{ pF, F}$	4.0 V,	10		10		10		ns
		$2.7 \text{ V} \leq \text{EV}_{DD}$ $2.3 \text{ V} \leq \text{V}_{b} \leq 2.3 \text{ V}$ $C_{b} = 20 \text{ pF}, \text{ F}$	2.7 V,	10		10		10		ns
Delay time from SCKp↓ to SOp output Note 1	tkso1	$4.0 \text{ V} \leq \text{EV}_{DD}$ $2.7 \text{ V} \leq \text{V}_{b} \leq 4.0 \text{ C}$ $C_{b} = 20 \text{ pF, F}$	o ≤ 5.5 V, 4.0 V,		60		60		60	ns
		$2.7 \text{ V} \le \text{EV}_{DD}$ $2.3 \text{ V} \le \text{V}_{b} \le 2$ $C_{b} = 20 \text{ pF, F}$	o < 4.0 V, 2.7 V,		130		130		130	ns

(Notes, Caution, and Remarks are listed on the next page.)

CSI mode connection diagram (during communication at different potential)



- Remarks 1. $R_b[\Omega]$:Communication line (SOp) pull-up resistance, $C_b[F]$: Communication line (SOp) load capacitance, $V_b[V]$: Communication line voltage
 - **2.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
 - 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13))
 - **4.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

(10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode) (2/2)

(Ta = -40 to +85°C, 1.8 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Conditions	HS (high	•	`	/-speed Mode	LV (low main)	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	tsu:dat	$\begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{aligned}$	1/f _{MCK} + 135 Note 3		1/fmck + 190 Note 3		1/fmck + 190 Note 3		kHz
		$\label{eq:section} \begin{split} 2.7 \ V &\leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V &\leq V_b \leq 2.7 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	1/f _{MCK} + 135 Note 3		1/fmck + 190 Note 3		1/fmck + 190 Note 3		kHz
		$ \begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 100 \; pF, \; R_b = 2.8 \; k\Omega \end{aligned} $	1/f _{MCK} + 190 Note 3		1/fmck + 190 Note 3		1/fmck + 190 Note 3		kHz
		$\label{eq:section} \begin{split} 2.7 \ V &\leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V &\leq V_b \leq 2.7 \ V, \\ C_b &= 100 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	1/f _{MCK} + 190 Note 3		1/fMCK + 190 Note 3		1/fmck + 190 Note 3		kHz
		$ \begin{aligned} &1.8 \; V \leq EV_{DD0} < 3.3 \; V, \\ &1.6 \; V \leq V_b \leq 2.0 \; V^{\text{Note 2}}, \\ &C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{aligned} $	1/f _{MCK} + 190 Note 3		1/fMCK + 190 Note 3		1/fmck + 190 Note 3		kHz
Data hold time (transmission)	thd:dat	$ \begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{aligned} $	0	305	0	305	0	305	ns
		$ \begin{aligned} &2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ &2.3 \; V \leq V_b \leq 2.7 \; V, \\ &C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{aligned} $	0	305	0	305	0	305	ns
		$ \begin{cases} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 100 \; pF, \; R_b = 2.8 \; k\Omega \end{cases} $	0	355	0	355	0	355	ns
		eq:second-seco	0	355	0	355	0	355	ns
		$ \begin{aligned} &1.8 \; V \leq EV_{DD0} < 3.3 \; V, \\ &1.6 \; V \leq V_b \leq 2.0 \; V^{\text{Note 2}}, \\ &C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{aligned} $	0	405	0	405	0	405	ns

Notes 1. The value must also be equal to or less than $f_{MCK}/4$.

- 2. Use it with $EV_{DD0} \ge V_b$.
- 3. Set the fmck value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the TTL input buffer and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 128-pin products)) mode for the SDAr pin and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 128-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

2.8 Flash Memory Programming Characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	fclk	1.8 V ≤ VDD ≤ 5.5 V	1		32	MHz
Number of code flash rewrites	Cerwr	Retained for 20 years TA = 85°C	1,000			Times
Number of data flash rewrites		Retained for 1 years TA = 25°C		1,000,000		
		Retained for 5 years TA = 85°C	100,000			
		Retained for 20 years TA = 85°C	10,000			

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite.

- The retaining years are until next rewrite after the rewrite.
- 2. When using flash memory programmer and Renesas Electronics self programming library
- **3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

2.9 Dedicated Flash Memory Programmer Communication (UART)

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200	_	1,000,000	bps

3. ELECTRICAL SPECIFICATIONS (G: INDUSTRIAL APPLICATIONS $T_A = -40$ to +105°C)

This chapter describes the following electrical specifications.

Target products G: Industrial applications $T_A = -40$ to +105°C R5F100xxGxx

- Cautions 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 - 2. With products not provided with an EVDD0, EVDD1, EVSS0, or EVSS1 pin, replace EVDD0 and EVDD1 with VDD, or replace EVSS0 and EVSS1 with VSS.
 - 3. The pins mounted depend on the product. Refer to 2.1 Port Function to 2.2.1 Functions for each product.
 - 4. Please contact Renesas Electronics sales office for derating of operation under $T_A = +85^{\circ}C$ to $+105^{\circ}C$. Derating is the systematic reduction of load for the sake of improved reliability.

Remark When RL78/G13 is used in the range of $T_A = -40$ to +85°C, see CHAPTER 2 ELECTRICAL SPECIFICATIONS ($T_A = -40$ to +85°C).

There are following differences between the products "G: Industrial applications ($T_A = -40$ to $+105^{\circ}$ C)" and the products "A: Consumer applications, and D: Industrial applications".

Parameter	Aŗ	oplication
	A: Consumer applications, D: Industrial applications	G: Industrial applications
Operating ambient temperature	T _A = -40 to +85°C	T _A = -40 to +105°C
Operating mode Operating voltage range	HS (high-speed main) mode: $2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V} \textcircled{0}1 \text{ MHz to } 32 \text{ MHz}$ $2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V} \textcircled{0}1 \text{ MHz to } 16 \text{ MHz}$ $LS \text{ (low-speed main) mode:}$ $1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V} \textcircled{0}1 \text{ MHz to } 8 \text{ MHz}$ $LV \text{ (low-voltage main) mode:}$ $1.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V} \textcircled{0}1 \text{ MHz to } 4 \text{ MHz}$	HS (high-speed main) mode only: $2.7~V \le V_{DD} \le 5.5~V @ 1~MHz~to~32~MHz$ $2.4~V \le V_{DD} \le 5.5~V @ 1~MHz~to~16~MHz$
High-speed on-chip oscillator clock accuracy	1.8 V \leq V _{DD} \leq 5.5 V \pm 1.0%@ T _A = -20 to +85°C \pm 1.5%@ T _A = -40 to -20°C 1.6 V \leq V _{DD} $<$ 1.8 V \pm 5.0%@ T _A = -20 to +85°C \pm 5.5%@ T _A = -40 to -20°C	$2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$ $\pm 2.0\%$ \bigcirc T _A = +85 to +105°C $\pm 1.0\%$ \bigcirc T _A = -20 to +85°C $\pm 1.5\%$ \bigcirc T _A = -40 to -20°C
Serial array unit	UART CSI: fclk/2 (supporting 16 Mbps), fclk/4 Simplified I ² C communication	UART CSI: fclk/4 Simplified I ² C communication
IICA	Normal mode Fast mode Fast mode plus	Normal mode Fast mode
Voltage detector	Rise detection voltage: 1.67 V to 4.06 V (14 levels) Fall detection voltage: 1.63 V to 3.98 V (14 levels)	Rise detection voltage: 2.61 V to 4.06 V (8 levels) Fall detection voltage: 2.55 V to 3.98 V (8 levels)

(Remark is listed on the next page.)



(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products (Ta = -40 to $+105^{\circ}$ C, 2.4 V \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 V, Vss = EV_{SS0} = EV_{SS1} = 0 V) (1/2)

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit		
Supply	I _{DD1}	Operating	HS (high-	fin = 32 MHz Note 3	Basic	V _{DD} = 5.0 V		2.3		mA		
Current Note 1		mode	speed main) mode Note 5	opera n	operatio n	V _{DD} = 3.0 V		2.3		mA		
					Normal	V _{DD} = 5.0 V		5.2	9.2	mA		
					operatio n	V _{DD} = 3.0 V		5.2	9.2	mA		
				fih = 24 MHz Note 3	Normal	V _{DD} = 5.0 V		4.1	7.0	mA		
					operatio n	V _{DD} = 3.0 V		4.1	7.0	mA		
				fin = 16 MHz ^{Note 3}	Normal	V _{DD} = 5.0 V		3.0	5.0	mA		
					operatio n	V _{DD} = 3.0 V		3.0	5.0	mA		
			HS (high-	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		3.4	5.9	mA		
			speed main) mode Note 5	V _{DD} = 5.0 V	operatio n	Resonator connection		3.6	6.0	mA		
				$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		3.4	5.9	mA		
				V _{DD} = 3.0 V	operatio n	Resonator connection		3.6	6.0	mA		
				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		2.1	3.5	mA		
				V _{DD} = 5.0 V	operatio n	Resonator connection		2.1	3.5	mA		
				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		2.1	3.5	mA		
			V DD - 0.0 V	operatio n	Resonator connection		2.1	3.5	mA			
			Subsystem clock operation	fsub = 32.768 kHz	Normal Square wave input operation Resonator connection		4.8	5.9	μΑ			
				$T_A = -40^{\circ}C$				4.9	6.0	μΑ		
				fsub = 32.768 kHz	Normal	Square wave input		4.9	5.9	μΑ		
			T _A = +25°C	operatio n	Resonator connection		5.0	6.0	μΑ			
			fsub = 32.768 kHz	Normal operation	Square wave input		5.0	7.6	μΑ			
			T _A = +50°C		Resonator connection		5.1	7.7	μΑ			
			fsuB = 32.768 kHz	Normal	Square wave input		5.2	9.3	μΑ			
			Note 4 $T_A = +70^{\circ}C$	operatio n	Resonator connection		5.3	9.4	μА			
				fsuB = 32.768 kHz	Normal	Square wave input		5.7	13.3	μΑ		
				Note 4 $T_A = +85^{\circ}C$	operatio n	Resonator connection		5.8	13.4	μΑ		
				fsuв = 32.768 kHz	Normal	Square wave input		10.0	46.0	μΑ		
								Note 4 TA = +105°C	operatio n	Resonator connection		10.0

(Notes and Remarks are listed on the next page.)

(7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol	Conditions		HS (high-spec	Unit	
				MIN.	MAX.	
SCKp cycle time Note 1	tkcy2	$4.0~V \le EV_{DD0} \le 5.5$	24 MHz < fмск	28/fмск		ns
		$V, \\ 2.7 V \leq V_b \leq 4.0 V$	20 MHz < fмcк ≤ 24 MHz	24/fмск		ns
			8 MHz < fмcк ≤ 20 MHz	20/fмск		ns
			4 MHz < fмcк ≤ 8 MHz	16/fмск		ns
			fмcк ≤ 4 MHz	12/fмск		ns
		2.7 V ≤ EV _{DD0} < 4.0	24 MHz < fмск	40/fмск		ns
		V,	20 MHz < fмcк ≤ 24 MHz	32/fмск		ns
		$2.3~V \leq V_b \leq 2.7~V$	16 MHz < fмск ≤ 20 MHz	28/fмск		ns
			8 MHz < fмск ≤ 16 MHz	24/fмск		ns
			4 MHz < fмcк ≤ 8 MHz	16/fмск		ns
			fмcк ≤ 4 MHz	12/fмск		ns
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3$	24 MHz < fмск	96/fмск		ns
		V,	20 MHz < fмск ≤ 24 MHz	72/fмск		ns
		$1.6~V \le V_b \le 2.0~V$	16 MHz < fмcк ≤ 20 MHz	64/ƒмск		ns
			8 MHz < fмск ≤ 16 MHz	52/fмск		ns
			4 MHz < fмcк ≤ 8 MHz	32/fмск		ns
			fмcк ≤ 4 MHz	20/fмск		ns
SCKp high-/low-level width	tкн2, tкL2	$\begin{aligned} 4.0 & \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}, \\ 2.7 & \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V} \\ \\ 2.7 & \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 & \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V} \end{aligned}$		tkcy2/2 - 24		ns
				txcy2/2 - 36		ns
		$2.4 \ V \le EV_{DD0} < 3.$ $1.6 \ V \le V_b \le 2.0 \ V$		tkcy2/2 - 100		ns
SIp setup time (to SCKp↑) Note2	tsık2	$4.0 \ V \le EV_{DD0} \le 5.0$ $2.7 \ V \le V_b \le 4.0 \ V$	*	1/fмск + 40		ns
				1/fмск + 40		ns
		$2.4 \ V \le EV_{DD0} < 3.$ $1.6 \ V \le V_b \le 2.0 \ V$		1/fмск + 60		ns
SIp hold time (from SCKp↑) Note 3	tksi2			1/fmck + 62		ns
Delay time from SCKp↓ to SOp output Note 4		$ \begin{aligned} 4.0 \ V &\leq EV_{\text{DDO}} \leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b &= 30 \ pF, \ R_b = 1.4 \ k\Omega \end{aligned} $			2/fмск + 240	ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 2$	0 V, 2.3 V \leq V _b \leq 2.7 V, 2.7 kΩ		2/fмск + 428	ns
		$2.4 \text{ V} \le \text{EV}_{\text{DDO}} < 3.$ $C_b = 30 \text{ pF}, R_b = 5$	3 V, 1.6 V ≤ V _b ≤ 2.0 V 5.5 kΩ		2/fмск + 1146	ns

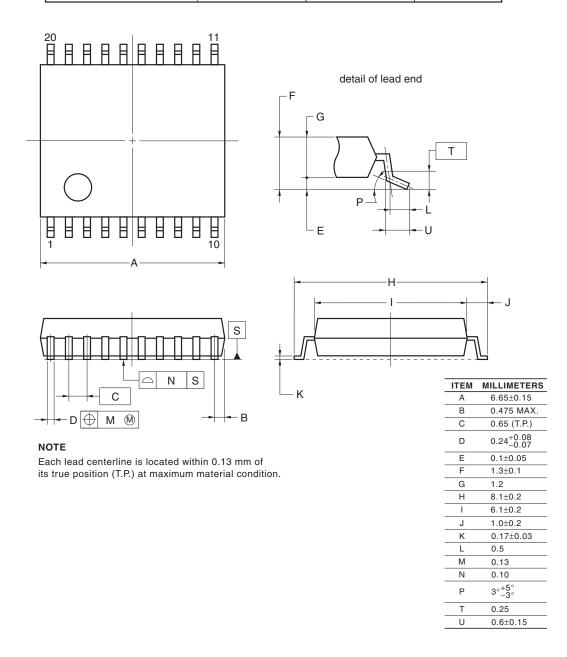
(Notes, Caution and Remarks are listed on the next page.)

4. PACKAGE DRAWINGS

4.1 20-pin Products

R5F1006AASP, R5F1006CASP, R5F1006DASP, R5F1006EASP R5F1016AASP, R5F1016CASP, R5F1016DASP, R5F1016EASP R5F1006ADSP, R5F1006CDSP, R5F1006DDSP, R5F1006EDSP R5F1016ADSP, R5F1016CDSP, R5F1016DDSP, R5F1016EDSP R5F1006AGSP, R5F1006CGSP, R5F1006DGSP, R5F1006EGSP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]	
P-LSSOP20-0300-0.65	PLSP0020JC-A	S20MC-65-5A4-3	0.12	



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R5F100GAANA, R5F100GCANA, R5F100GDANA, R5F100GEANA, R5F100GFANA, R5F100GHANA, R5F100GHANA, R5F100GKANA, R5F100GKANA, R5F100GKANA, R5F100GKANA

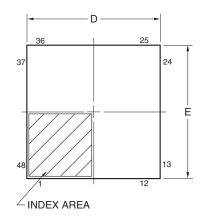
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R5F100GADNA, R5F100GCDNA, R5F100GDDNA, R5F100GEDNA, R5F100GFDNA, R5F100GDNA, R5F100GHDNA, R5F100GJDNA, R5F100GKDNA, R5F100GLDNA

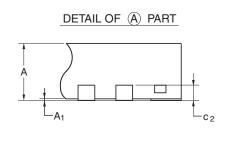
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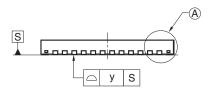
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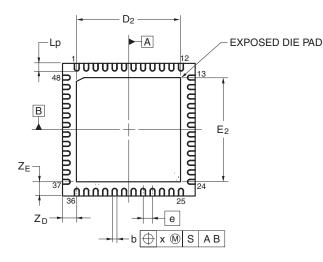
JEITA Package code	RENESAS code	Previous code	MASS(TYP.)[g]
P-HWQFN48-7x7-0.50	PWQN0048KB-A	48PJN-A P48K8-50-5B4-6	0.13











Referance	Dimension in Millimeters			
Symbol	Min	Nom	Max	
D	6.95	7.00	7.05	
Е	6.95	7.00	7.05	
Α			0.80	
A ₁	0.00			
b	0.18	0.25	0.30	
е		0.50		
Lp	0.30	0.40	0.50	
Х			0.05	
у			0.05	
Z _D		0.75		
Z _E		0.75		
C ₂	0.15	0.20	0.25	
D ₂		5.50		
E ₂		5.50	_	

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		Description	
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3.00	Aug 02, 2013	81	Modification of figure of AC Timing Test Points
		81	Modification of description and note 3 in (1) During communication at same potential (UART mode)
		83	Modification of description in (2) During communication at same potential (CSI mode)
		84	Modification of description in (3) During communication at same potential (CSI mode)
		85	Modification of description in (4) During communication at same potential (CSI mode) (1/2)
		86	Modification of description in (4) During communication at same potential (CSI mode) (2/2)
		88	Modification of table in (5) During communication at same potential (simplified I ² C mode) (1/2)
		89	Modification of table and caution in (5) During communication at same potential (simplified I ² C mode) (2/2)
		91	Modification of table and notes 1 and 4 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)
		92, 93	Modification of table and notes 2 to 7 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)
		94	Modification of remarks 1 to 4 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)
		95	Modification of table in (7) Communication at different potential (2.5 V, 3 V) (CSI mode) (1/2)
		96	Modification of table and caution in (7) Communication at different potential (2.5 V, 3 V) (CSI mode) (2/2)
		97	Modification of table in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (1/3)
		98	Modification of table, note 1, and caution in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (2/3)
		99	Modification of table, note 1, and caution in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (3/3)
		100	Modification of remarks 3 and 4 in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (3/3)
		102	Modification of table in (9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (1/2)
		103	Modification of table and caution in (9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (2/2)
		106	Modification of table in (10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I ² C mode) (1/2)
		107	Modification of table, note 1, and caution in (10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I ² C mode) (2/2)
		109	Addition of (1) I ² C standard mode
		111	Addition of (2) I ² C fast mode
		112	Addition of (3) I ² C fast mode plus
		112	Modification of IICA serial transfer timing
		113	Addition of table in 2.6.1 A/D converter characteristics
		113	Modification of description in 2.6.1 (1)
		114	Modification of notes 3 to 5 in 2.6.1 (1)
		115	Modification of description and notes 2, 4, and 5 in 2.6.1 (2)
		116	Modification of description and notes 3 and 4 in 2.6.1 (3)
		117	Modification of description and notes 3 and 4 in 2.6.1 (4)

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		118	Modification of table and note in 2.6.3 POR circuit characteristics
		119	Modification of table in 2.6.4 LVD circuit characteristics
		120	Modification of table of LVD Detection Voltage of Interrupt & Reset Mode
		120	Renamed to 2.6.5 Power supply voltage rising slope characteristics
		122	Modification of table, figure, and remark in 2.10 Timing Specs for Switching Flash Memory Programming Modes
		123	Modification of caution 1 and description
		124	Modification of table and remark 3 in Absolute Maximum Ratings (T _A = 25°C)
		126	Modification of table, note, caution, and remark in 3.2.1 X1, XT1 oscillator characteristics
		126	Modification of table in 3.2.2 On-chip oscillator characteristics
		127	Modification of note 3 in 3.3.1 Pin characteristics (1/5)
		128	Modification of note 3 in 3.3.1 Pin characteristics (2/5)
		133	Modification of notes 1 and 4 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products (1/2)
		135	Modification of notes 1, 5, and 6 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products (2/2)
		137	Modification of notes 1 and 4 in (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products (1/2)
		139	Modification of notes 1, 5, and 6 in (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products (2/2)
		140	Modification of (3) Peripheral Functions (Common to all products)
		142	Modification of table in 3.4 AC Characteristics
		143	Addition of Minimum Instruction Execution Time during Main System Clock Operation
		143	Modification of figure of AC Timing Test Points
		143	Modification of figure of External System Clock Timing
		145	Modification of figure of AC Timing Test Points
		145	Modification of description, note 1, and caution in (1) During communication at same potential (UART mode)
		146	Modification of description in (2) During communication at same potential (CSI mode)
		147	Modification of description in (3) During communication at same potential (CSI mode)
		149	Modification of table, note 1, and caution in (4) During communication at same potential (simplified I ² C mode)
		151	Modification of table, note 1, and caution in (5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)
		152 to 154	Modification of table, notes 2 to 6, caution, and remarks 1 to 4 in (5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)
		155	Modification of table in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (1/3)
		156	Modification of table and caution in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (2/3)
		157, 158	Modification of table, caution, and remarks 3 and 4 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (3/3)
		160, 161	Modification of table and caution in (7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode)